

Topic 6

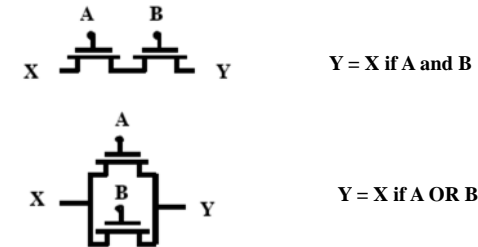
CMOS Static & Dynamic Logic Gates

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NMOS Transistors in Series/Parallel Connection

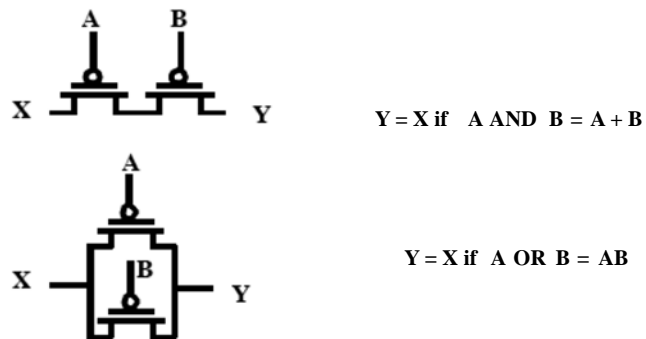
- Transistors can be thought as a switch controlled by its gate signal
- NMOS switch closes when switch control input is high



NMOS Transistors pass a “strong” 0 but a “weak” 1

PMOS Transistors in Series/Parallel Connection

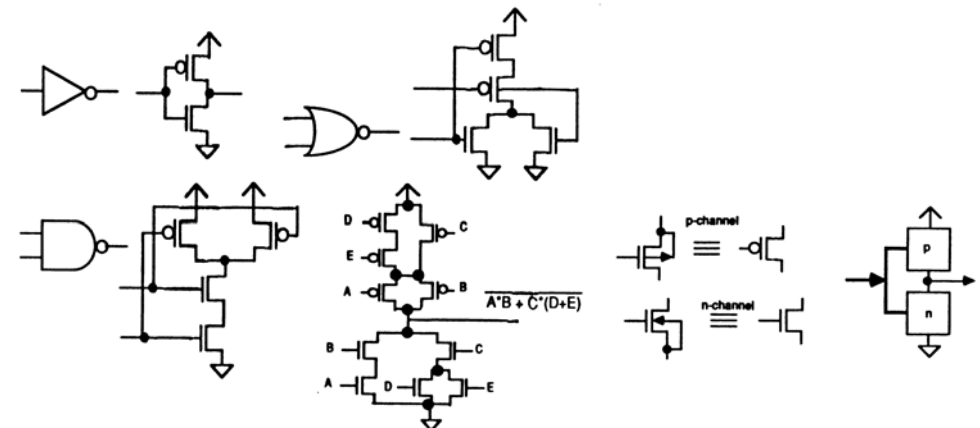
PMOS switch closes when switch control input is low



PMOS Transistors pass a “strong” 1 but a “weak” 0

Static CMOS Circuit

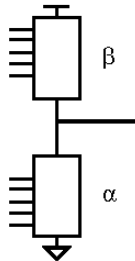
- Basic CMOS combinational circuits consist of:
 - Complementary pull-up (p-type) and pull-down (n-type)



Static CMOS

To build a logic gate $\bar{f}(x_1, \dots, x_n)$, need to build two switch networks:

The pullup network connects the output to V_{DD} when f is false.



The pulldown network connects the output to GND when f is true.

Pulldown

$$\alpha(x_1, \dots, x_n) = f(x_1, \dots, x_n)$$

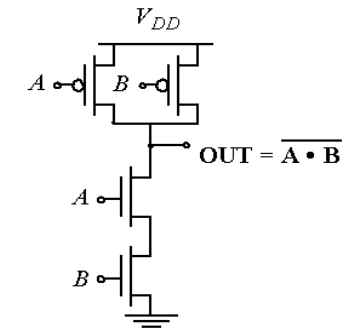
Pullup

$$\beta(\bar{x}_1, \dots, \bar{x}_n) = \bar{f}(x_1, \dots, x_n) \quad (\text{since pMOS invert inputs})$$

Example Gate: NAND

| A | B | Out |
|---|---|-----|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

Truth Table of a 2 input NAND gate



PDN: $G = A B \Rightarrow$ Conduction to GND

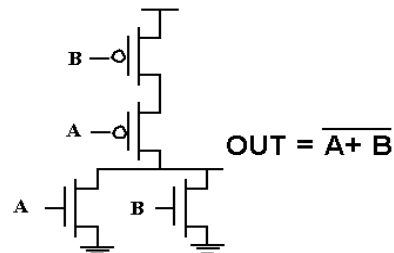
PUN: $F = \bar{A} + \bar{B} = \overline{AB} \Rightarrow$ Conduction to V_{DD}

$$G(In_1, In_2, In_3, \dots) \equiv F(\bar{In}_1, \bar{In}_2, \bar{In}_3, \dots)$$

Example Gate: NOR

| A | B | Out |
|---|---|-----|
| 0 | 0 | 1 |
| 0 | 1 | 0 |
| 1 | 0 | 0 |
| 1 | 1 | 0 |

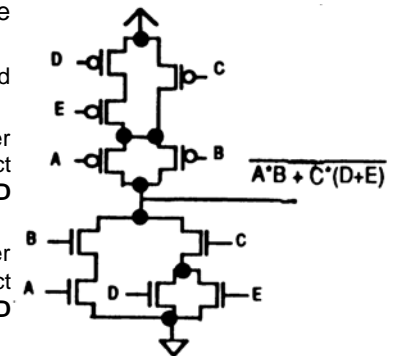
Truth Table of a 2 input NOR gate



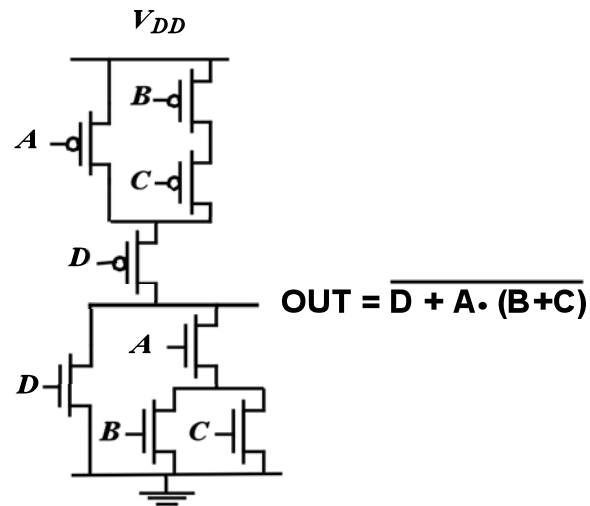
Complex Gate

- We can form complex combinational circuit function in a complementary tree. The procedure to construct a complementary tree is as follow:-

- Express the boolean expression in an inverted form
- For the n-transistor tree, working from the inner-most bracket to the outer-most term, connect the **OR** term transistors in parallel, and the **AND** term transistors in series
- For the p-transistor tree, working from the inner-most bracket to the outer-most term, connect the **OR** term transistors in series, and the **AND** term transistors in parallel



Example Gate: COMPLEX CMOS GATE



Properties of Complementary CMOS Gates

1) High noise margins

V_{OH} and V_{OL} are at V_{DD} and GND , respectively.

2) No static power consumption

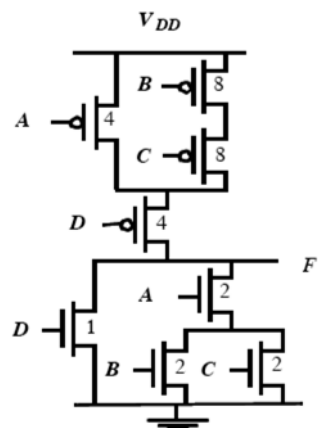
There never exists a direct path between V_{DD} and V_{SS} (GND) in steady-state mode

3) Comparable rise and fall times:

(under the appropriate scaling conditions)

Transistor Sizing

- for symmetrical response (dc, ac)
- for performance

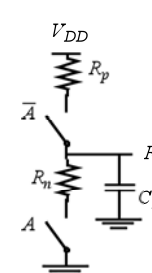


Input Dependent

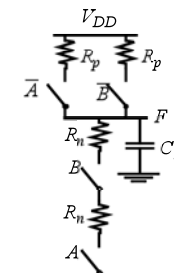
Focus on worst-case

- assume $\mu_n = 2 \cdot \mu_p$ (i.e. n-channel transistors has 2 times the transconductance as that of p-channel.)

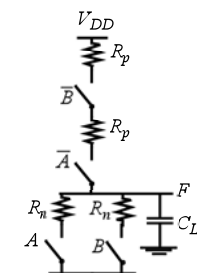
Propagation Delay Analysis - The Switch Model



(a) Inverter



(b) 2-input NAND



(c) 2-input NOR

$$t_p = 0.69 R_{on} C_L$$

(assuming that C_L dominates!)

What is the Value of R_{on} ?

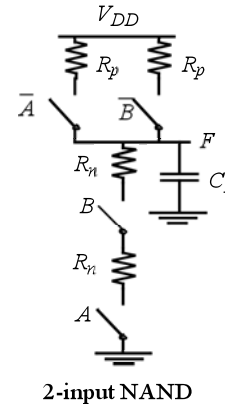
- Depends strongly on the operating region
- For hand analysis use a fixed value of R which is the average of the two end points of the transition
- Similar to the previous approach of averaging currents

EXAMPLE: For t_{pHL} for an inverter, the R_{on} is:

$$R_{on} = \frac{1}{2}(R_{NMOS}(V_{out} = V_{DD}) + R_{NMOS}(V_{out} = V_{DD}/2))$$

$$= \frac{1}{2} \left(\left(\frac{V_{DS}}{I_D} \right)_{V_{out} = V_{DD}} + \left(\frac{V_{DS}}{I_D} \right)_{V_{out} = V_{DD}/2} \right)$$

Analysis of Propagation Delay



2-input NAND

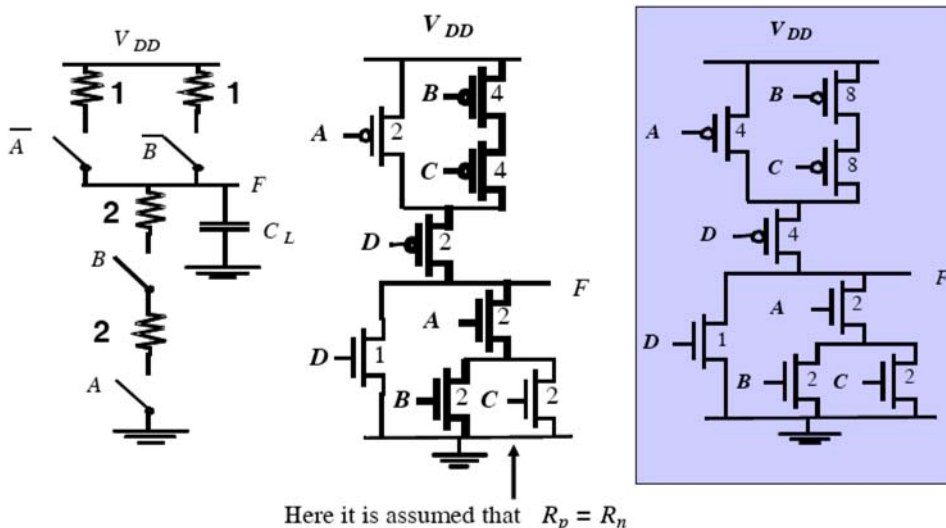
1. Assume $R_n = R_p$ = resistance of minimum sized NMOS inverter
2. Determine "Worst Case Input" transition (Delay depends on input values)
3. Example: t_{pLH} for 2input NAND
 - Worst case when only ONE PMOS Pulls up the output node
 - For 2 PMOS devices in parallel, the resistance is lower

$$t_{pLH} = 0.69 R_p C_L$$

4. Example: t_{pHL} for 2input NAND
 - Worst case : TWO NMOS in series

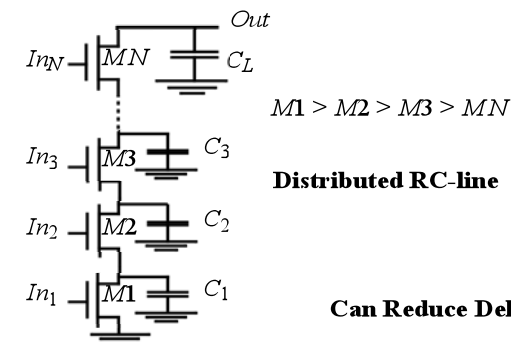
$$t_{pHL} = 0.69 (2R_n) C_L$$

Design for Worst Case



Fast Complex Gate - Design Techniques

- Transistor Sizing:
As long as Fan-out Capacitance dominates
- Progressive Sizing:



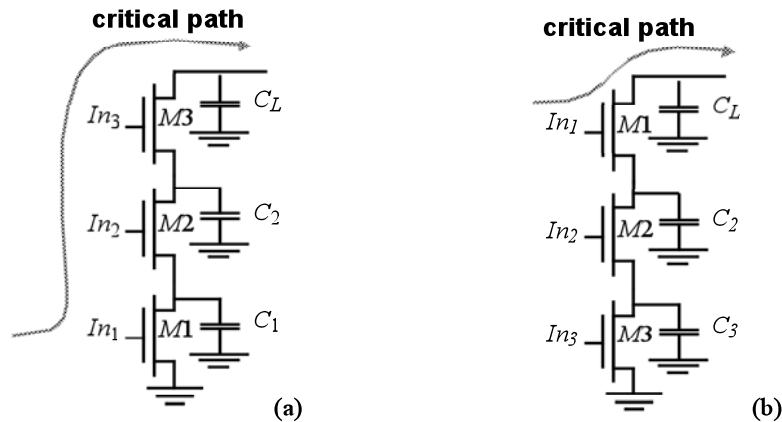
$$M1 > M2 > M3 > MN$$

Distributed RC-line

Can Reduce Delay with more than 30%!

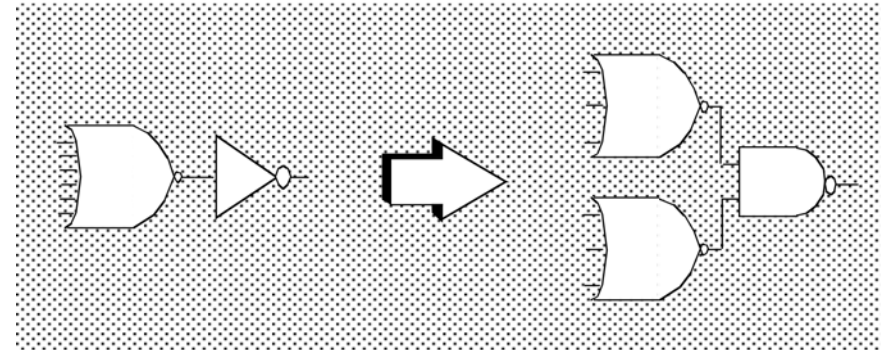
Fast Complex Gate - Design Techniques (2)

• Transistor Ordering



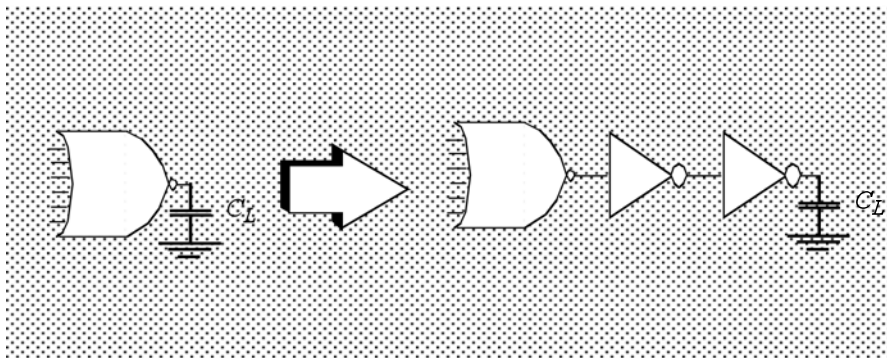
Fast Complex Gate - Design Techniques (3)

• Improved Logic Design

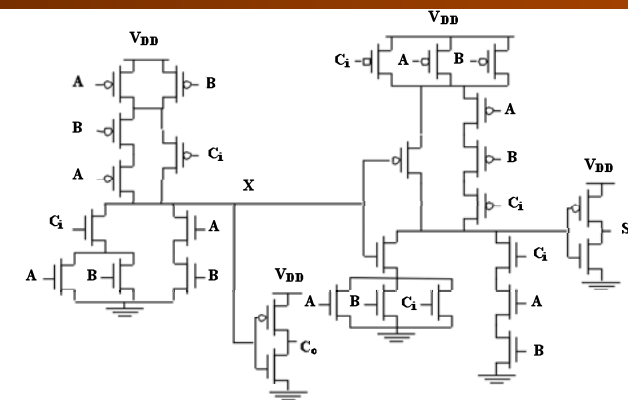


Fast Complex Gate - Design Techniques (4)

• Buffering: Isolate Fan-in from Fan-out



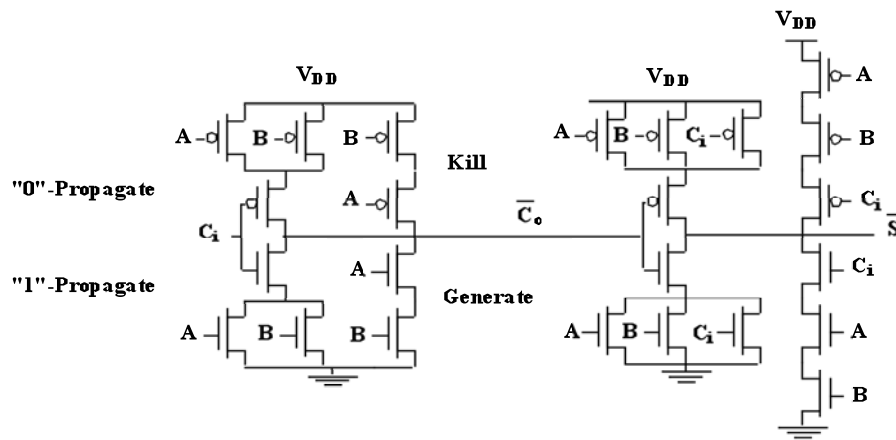
Example: Full Adder



$$C_o = AB + C_i(A+B)$$

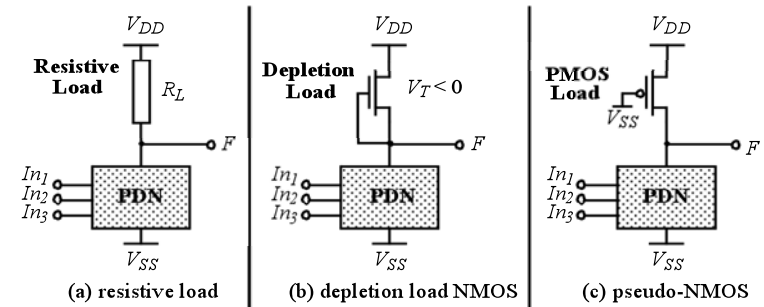
28 transistors

A Revised Adder Circuit



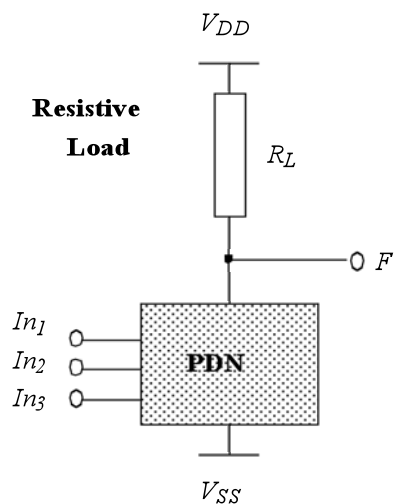
24 transistors

Ratioed Logic



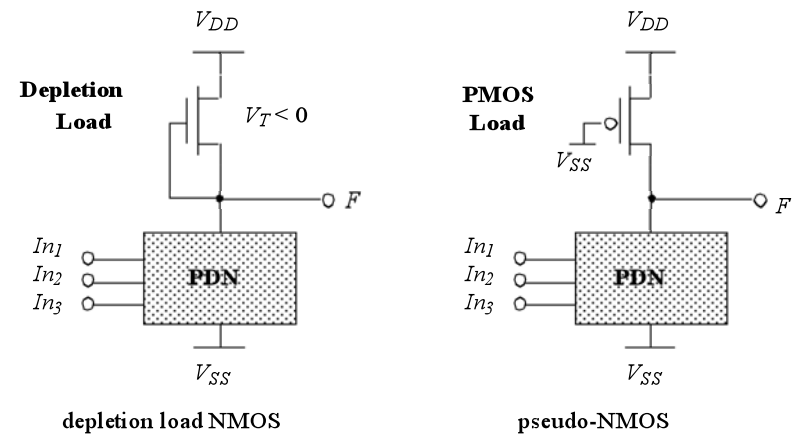
Goal: to reduce the number of devices over complementary CMOS

Ratioed Logic



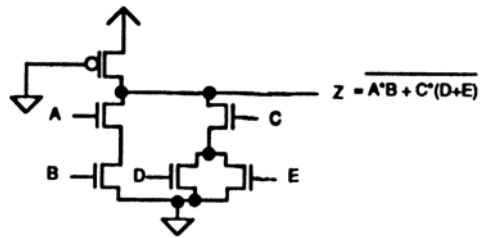
- N transistors + Load
- $V_{OH} = V_{DD}$
- $V_{OL} = \frac{R_{PN}}{R_{PN} + R_L}$
- Asymmetrical response
- Static power consumption
- $t_{pL} = 0.69 R_L C_L$

Active Loads



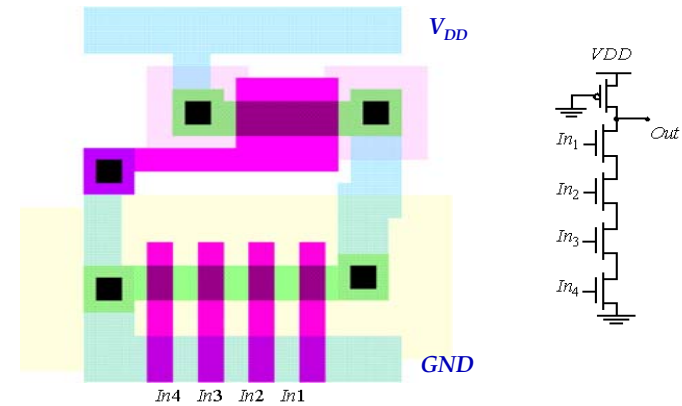
Pseudo NMOS

- Disadvantages of previous circuit :
 - Almost twice as many transistors as equivalent NMOS implementation.
 - If there are too many series transistors in the tree, switching speed is reduced.
- Try a pseudo NMOS circuit:-



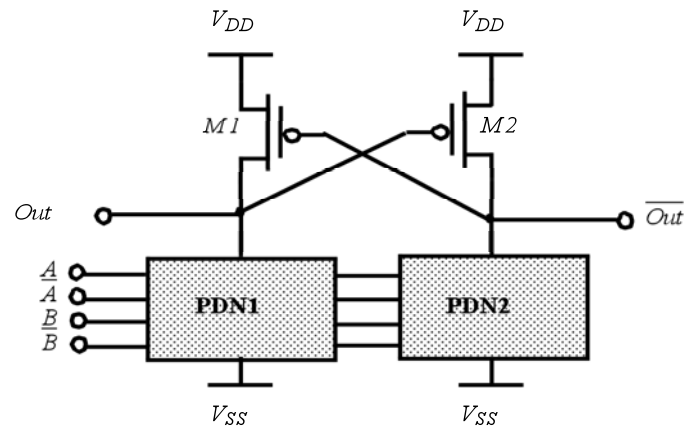
- The pull-up p-channel transistor is always conducting.
 - Disadvantages: high d.c. dissipation & slow rise time.

Pseudo-NMOS NAND Gate



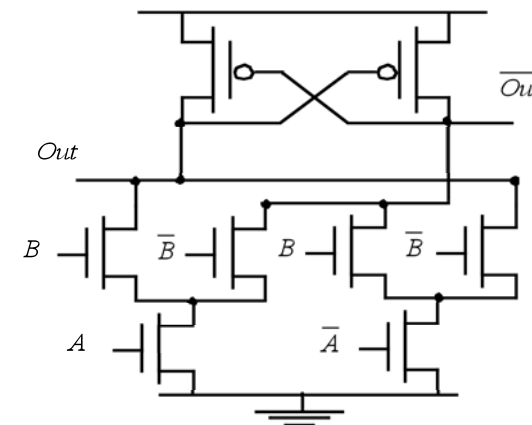
$$C_{L,pseudo} = 0.5 C_{L,CMOS} \text{ (Fan-out of 1)}$$

Improved Loads (1)



Dual Cascode Voltage Switch Logic (DCVSL)

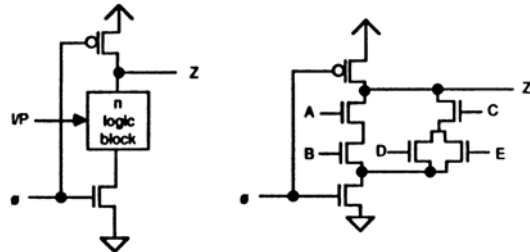
Example



XOR-NXOR gate

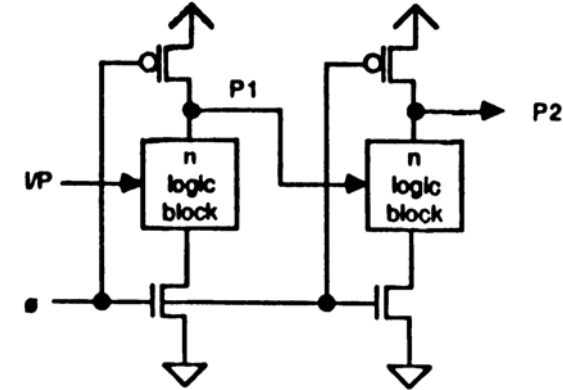
Dynamic Logic

- There is another class of logic gates which relies on the use of a clock signal. This class of circuit is known as *dynamic circuits*. The clock signal is used to divide the gate operation into two halves. In the first half, the output node is **pre-charged** to a high or low logic state. In the second half of a clock cycle, the circuit **evaluates** the correct output state.
- When ϕ is low, Z is charged to high. When ϕ is high, n logic block evaluates input, and conditionally discharges Z. This circuit adds series resistance to the pull-down n-channel transistor, therefore the fall time is increased slightly.
- This circuit is *dynamic* because during evaluation, the output high level at Z is maintained by the stray capacitance at the output node. If ϕ stays high (i.e. evaluation period) for a long time, Z may eventually discharge to a low logic level.



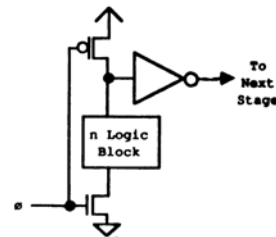
Problem with Cascading Dynamic Logic

- Problem with cascading such as a circuit:-
 - Inputs can only be changed when ϕ is low and must be stable when ϕ is high.
 - When ϕ is low, both P1 and P2 are precharged to a high voltage. However when ϕ is high, delay through on the output P1 may erroneously discharge P2.



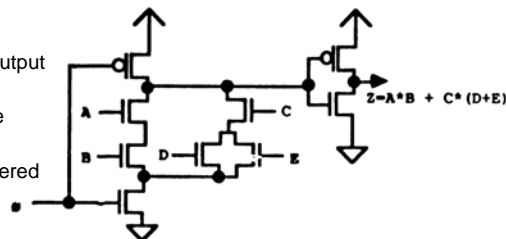
CMOS Domino Logic

- Solution to the above problem:-
 - Add an inverter to ensure that the output is low during precharge, and prevent the next stage from evaluating, until the current stage has finished evaluation.
 - This ensures that each stage (at the output of the inverter) will make at most a single transition from 0 -> 1.
 - When many stages are cascaded, evaluation proceeds from one stage to the next - similar to dominos falling one after another.



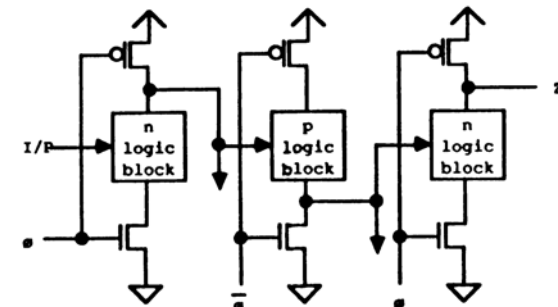
Disadvantages of domino logic:-

- Only non-inverting logic is possible, i.e. output also high active
- Each gate needs an inverter; hence more transistors
- Suffer from charge sharing effect (considered later)



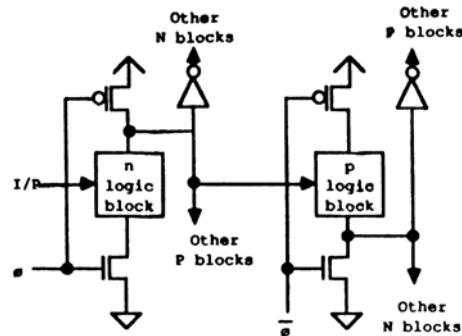
Alternating dynamic logic (1)

- Another possible scheme is to use alternate n and p logic blocks as shown below.
- In this scheme, each alternate stage is pre-charged high and low. Each stage uses alternate n and p transistors to implement the gate function. Stage 1 makes at most one high to low transition, while stage 2 makes at most one low to high transition for each evaluation. Since the p logic block will only change state if input is a low, this circuit behaves like the domino logic.



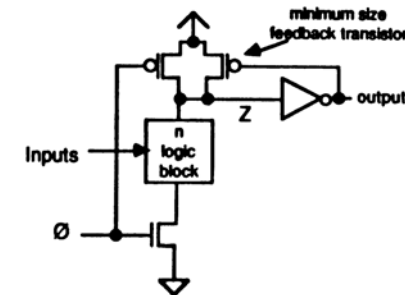
Alternating dynamic logic (2)

- A slight variation of this circuit is shown below, where an inverter is added per stage to increase flexibility. Here each stage can drive either n or p blocks and both low active and high active logic can be implemented.



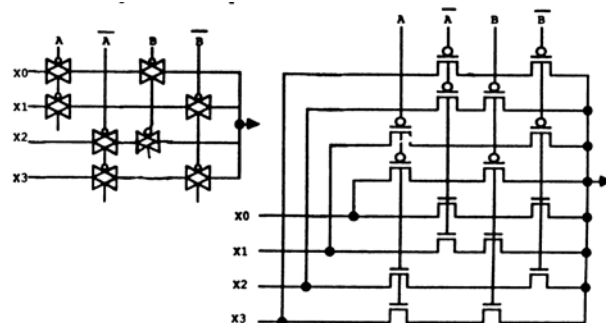
Making a Dynamic Gate static

- Finally, by adding a feedback pullup, we can make the circuit static.
- This circuit turns the originally **dynamic** gate into a **static** gate because the feedback transistor can maintain a logic high level at the node Z for an indefinite length of time. Without this feedback transistor, the charge stored at the node Z will eventually leak away.



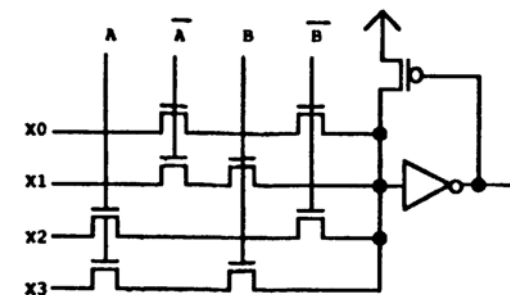
Pass Transistor Logic

- An alternative design style is to use pass transistors. The following is an example of a multiplexer.
- Complementary transmission gates are used here because n-channel pass transistors will pass 0 logic level well but, 1 logic level poorly. This is because in order for the n-transistor to be **ON**, V_{gs} must be greater than V_{th} . Therefore each series n transistor will degrade the 1 logic level by V_{th} . The opposite is true with p-channel pass transistors: 0 logic level is passed poorly.



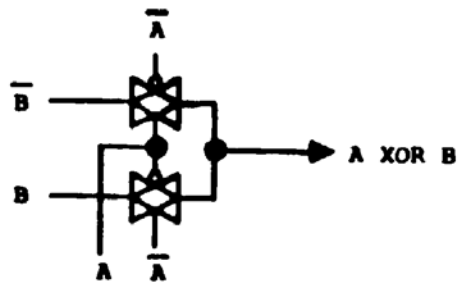
Pass Transistor Logic with feedback

- This circuit uses only n transistors, therefore it is economical on transistor count. In order to ensure that the 1 logic level is passed properly, a p pull-up transistor is added. This restores the 1 logic level at the input of the inverter.



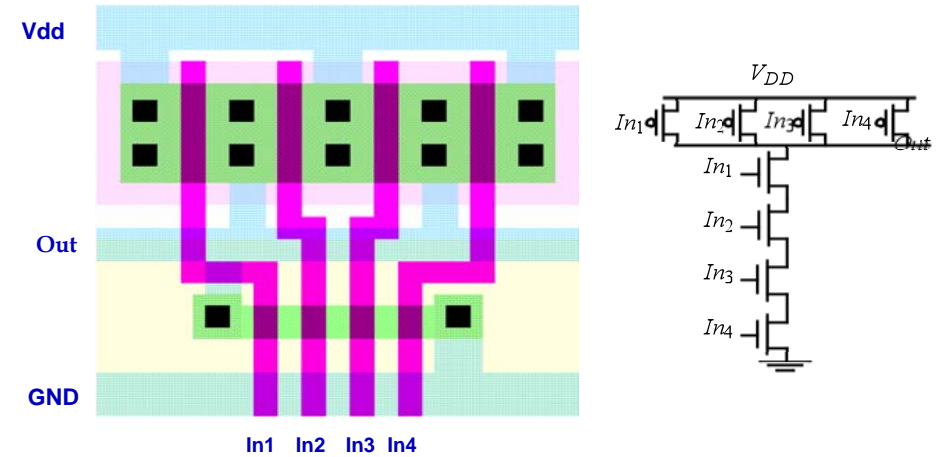
Pass Transistor XOR gate

- Pass transistor logic can sometimes be very economical in implementing logic functions. For example, an XOR gate can be implemented with just two transmission gates:-

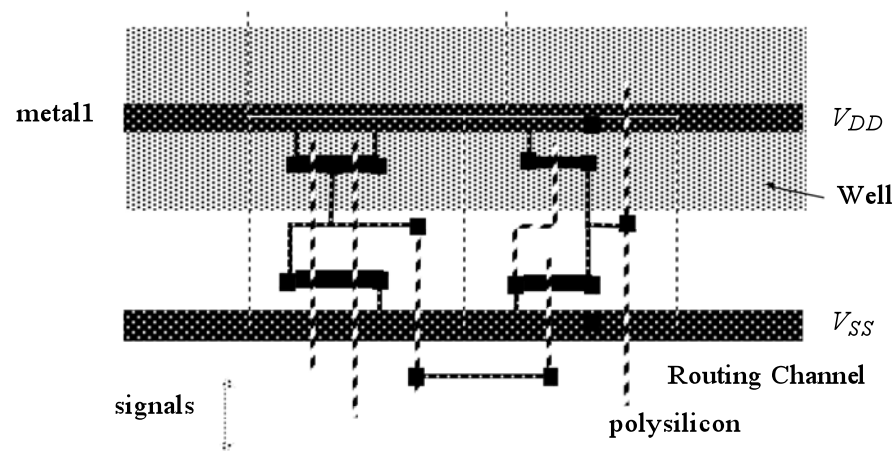


| A | B | XOR |
|---|---|-----|
| 0 | 0 | 0 |
| 1 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 1 | 0 |

4-input NAND Gate



Standard Cell Layout Methodology



Two Versions of (a+b).c

